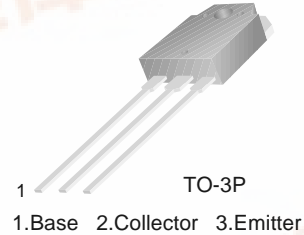


**FAIRCHILD**  
SEMICONDUCTOR®

## KSC3552

### High Voltage and High Reliability

- High Speed Switching
- Wide SOA



### NPN Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	1100	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	12	A
$I_{CP}$	Collector Current (Pulse)	30	A
$I_B$	Base Current	6	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	150	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CB0}$	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}, I_E = 0$	1100			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	800			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}, I_C = 0$	7			V
$V_{CEX(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 6\text{A}, I_{B1} = -I_{B2} = 1.2\text{A}$ $L = 500\mu\text{H}, \text{Clamped}$	800			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 800\text{V}, I_E = 0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			10	$\mu\text{A}$
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 0.8\text{A}$ $V_{CE} = 5\text{V}, I_C = 4\text{A}$	10 8		40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 6\text{A}, I_B = 1.2\text{A}$			2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 6\text{A}, I_B = 1.2\text{A}$			1.5	V
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		215		pF
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.8\text{A}$		15		MHz
$t_{ON}$	Turn ON Time	$V_{CC} = 400\text{V}$			0.5	$\mu\text{s}$
$t_{STG}$	Storage Time	$5I_{B1} = -2.5I_{B2} = I_C = 8\text{A}$			3	$\mu\text{s}$
$t_F$	Fall Time	$R_L = 50\Omega$			0.3	$\mu\text{s}$

### $h_{FE}$ Classification

Classification	N	R	O
$h_{FE}$	10 ~ 20	15 ~ 30	20 ~ 40



# Typical Characteristics

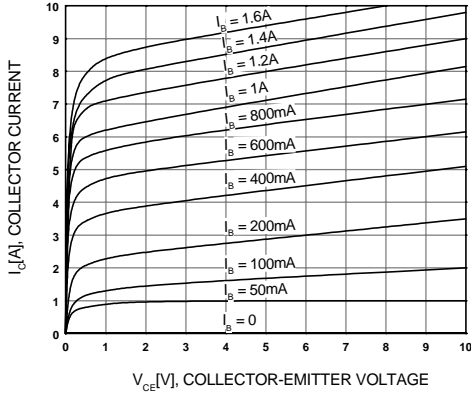


Figure 1. Static Characteristic

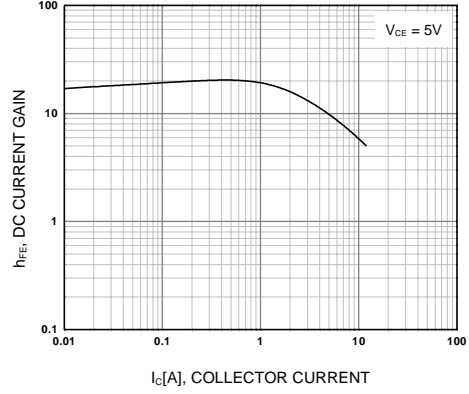


Figure 2. DC current Gain

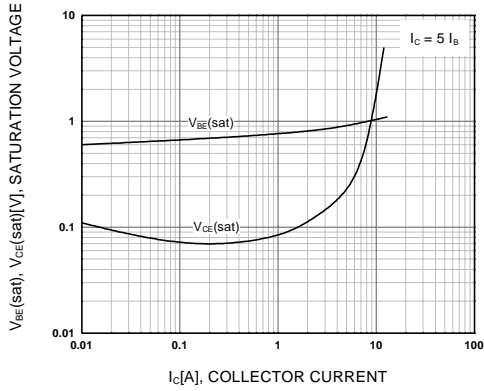


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

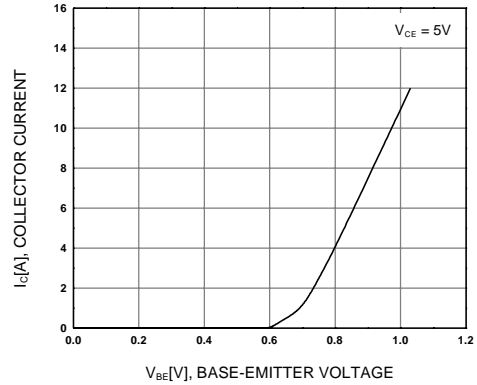


Figure 4. Base-Emitter on Voltage

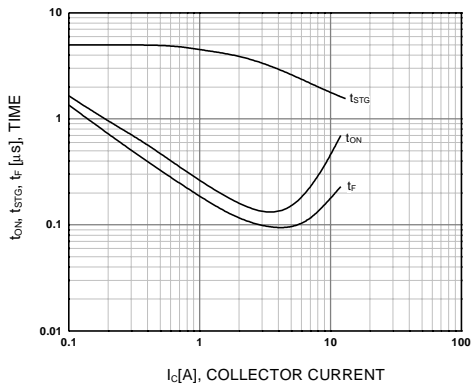


Figure 5. Turn On Time

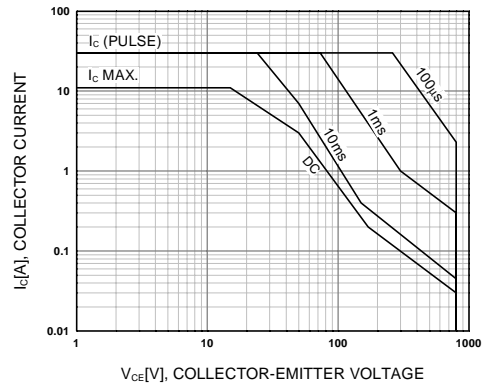


Figure 6. Safe Operating Area

### Typical Characteristics (Continued)

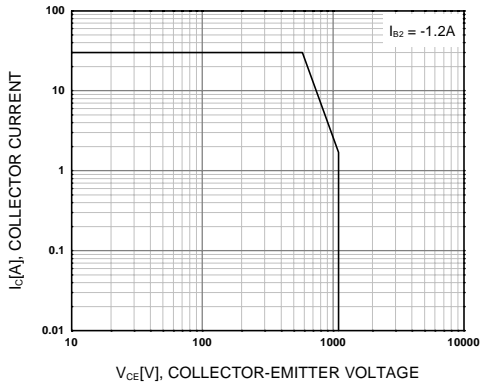


Figure 7. Reverse Bias Safe Operating Area

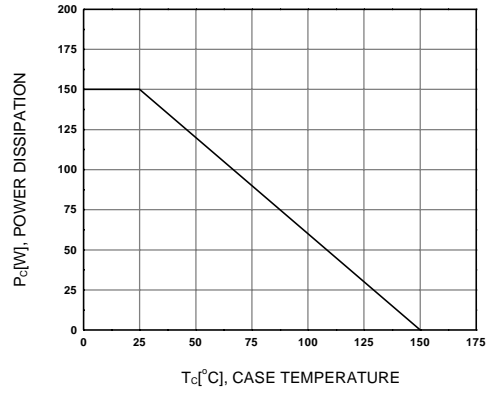
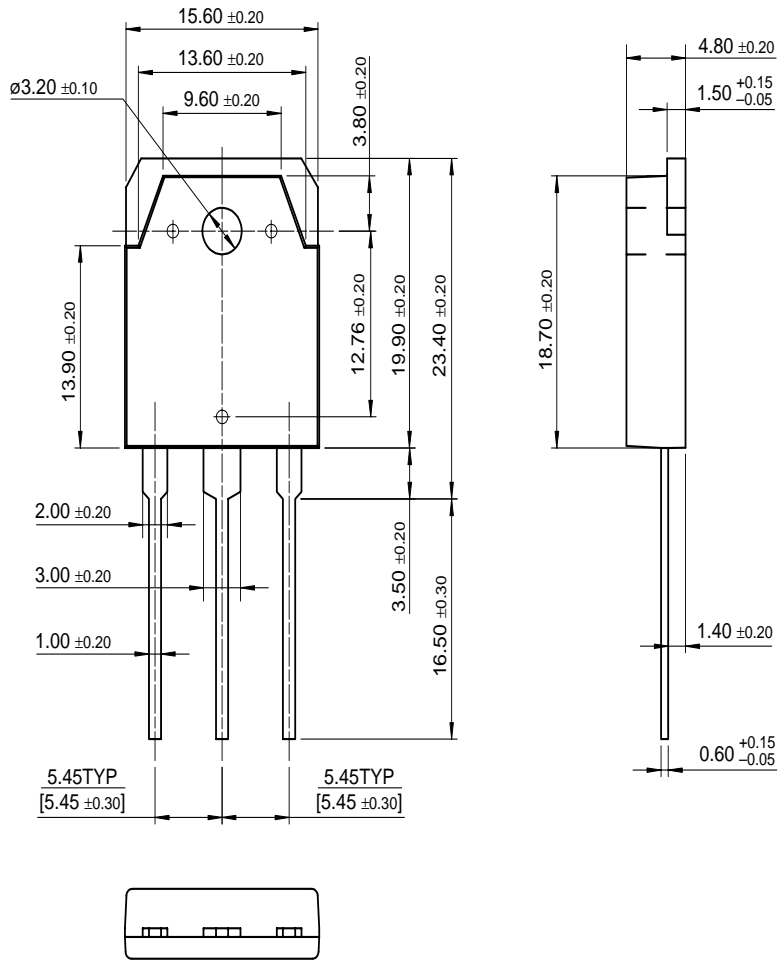


Figure 8. Power Derating

# Package Dimensions

## TO-3P



Dimensions in Millimeters

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